

# GaAs SP2T Absorptive Switch with ASIC Driver, DC-3.0 GHz

Rev. V10

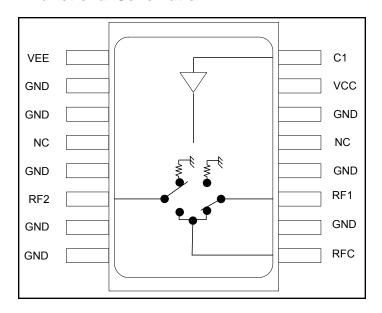
#### **Features**

- Typical Isolation: 30 dB (2,000 MHz) Typical Insertion Loss: .75 dB (2,000 MHz)
- ASIC TTL/CMOS Driver
- Low DC Power Consumption
- 50 Ohm Nominal Impedance
- Tape and Reel Packaging Available
- Test Boards Available
- SOIC-16 Package

# **Description**

M/A-COM's SW65-0313 is a GaAs MMIC absorptive SP2T switch with an integral silicon ASIC driver. This device is in a 16-lead plastic package. This switch offers excellent broadband performance and repeatability from DC to 3 GHz, while maintaining low DC power dissipation. The SW65-0313 is ideally suited for wireless infrastructure applications. Also available in a ceramic package with improved performance.

#### **Functional Schematic**



# Pin Configuration<sup>1</sup>

| Pin No. | Function        | Pin No. | Function        |
|---------|-----------------|---------|-----------------|
| 1       | V <sub>EE</sub> | 9       | RFC             |
| 2       | GND             | 10      | GND             |
| 3       | GND             | 11      | RF1             |
| 4       | NC              | 12      | GND             |
| 5       | GND             | 13      | NC              |
| 6       | RF2             | 14      | GND             |
| 7       | GND             | 15      | V <sub>CC</sub> |
| 8       | GND             | 16      | C1              |

NC = No Connection

# **Ordering Information**

| Part Number | Package           |  |
|-------------|-------------------|--|
| SW65-0313   | Bulk Packaging    |  |
| SW65-0313TR | 1000 piece reel   |  |
| SW65-0313TB | Sample Test Board |  |

Note: Reference Application Note M513 for reel size information.



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# Electrical Specifications: $T_A = 25$ °C, $Z_0 = 50\Omega$

| Parameter   | Test Conditions  | Units          | Min            | Тур                     | Max                     |
|---|--|----------------|----------------|-------------------------|-------------------------|
| Insertion Loss  | DC - 1.0 GHz<br>DC - 2.0 GHz<br>DC - 3.0 GHz                                     | dB<br>dB<br>dB | _<br>_<br>_    | 0.6<br>0.75<br>1.2      | 0.75<br>0.90<br>1.45    |
| Isolation<br>(All arms off)   | DC - 1.0 GHz<br>DC - 2.0 GHz<br>DC - 3.0 GHz                                     | dB<br>dB<br>dB | 35<br>27<br>21 | 38<br>30<br>24          | _<br>_<br>_             |
| VSWR  | DC - 1.0 GHz<br>DC - 2.0 GHz<br>DC - 3.0 GHz                                     |                | _              | 1.2:1<br>1.3:1<br>1.7:1 | 1.3:1<br>1.4:1<br>1.9:1 |
| T <sub>rise</sub> T <sub>fall</sub><br>T <sub>on</sub> T <sub>off</sub><br>Transients | 10%/90%, 90%/10% <sup>2</sup><br>50% TTL to 90%/10% RF<br>In-band (peak to peak) | ns<br>ns<br>mV |                | 15<br>50<br>50          | 50<br>150<br>150        |
| 1 dB Compression  | .05 GHz<br>.5 - 3.0 GHz  | dBm<br>dBm     | _              | +25<br>+30              | _                       |
| Input IP3   | Two tone inputs 0.05 GHz<br>Up to +5 dBm 0.5 - 3.0 GHz                           | dBm<br>dBm     | _              | +40<br>+46              | _                       |
| Vcc   | _  | V              | +4.5           | +5.0                    | 5.5                     |
| VEE   | _  | V              | -8.0           | -5.0                    | -4.75                   |
| V <sub>IL</sub><br>V <sub>IH</sub>  | LOW-level input voltage<br>HIGH-level input voltage                              | V              | 0.0<br>2.0     | _                       | 0.8<br>5.0              |
| lin (Input Leakage Current)   | $Vin = V_{CC}$ or GND  | uA             | -1.0           | _                       | 1.0                     |
| Icc<br>(Quiescent Supply Current)   | Vcntrl = V <sub>CC</sub> or GND  | uA             | _              | 250                     | 400                     |
| Δlcc<br>(Additional Supply Current Per<br>TTL Input Pin)                              | V <sub>CC</sub> = Max, Vcntrl = V <sub>CC</sub> - 2.1 V                          | mA             | _              | _                       | 1.0                     |
| lee   | VEE min to max, Vin = $V_{IL}$ or $V_{IH}$                                       | mA             | -1.0           | -0.2                    | _                       |

<sup>2.</sup> Decoupling capacitors (.01  $\mu F$ ) are required on the power supply lines.

<sup>•</sup> China Tel: +86.21.2407.1588 • India Tel: +91.80.4155721 Visit www.macomtech.com for additional data sheets and product information.



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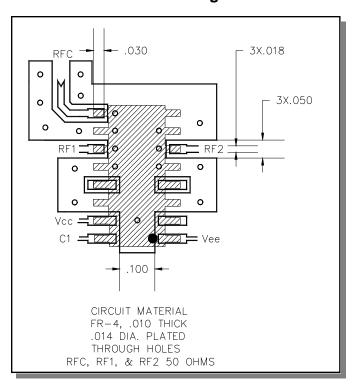
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# **Absolute Maximum Ratings**<sup>3,4</sup>

| Parameter  | Absolute Maximum                                  |  |  |
|--|---|--|--|
| Max. Input Power<br>0.05 GHz<br>0.5 - 3.0 GHz <sup>5</sup> | +27 dBm<br>+34 dBm                                |  |  |
| V <sub>CC</sub>  | $-0.5V \le V_{CC} \le +7.0V$                      |  |  |
| V <sub>EE</sub>  | -8.5V ≤ V <sub>EE</sub> ≤ +0.5V                   |  |  |
| V <sub>CC</sub> - V <sub>EE</sub>                          | -0.5V ≤ V <sub>CC</sub> - V <sub>EE</sub> ≤ 14.5V |  |  |
| Vin <sup>6</sup>   | -0.5V ≤ Vin ≤ V <sub>CC</sub> + 0.5V              |  |  |
| Operating Temperature                                      | -40°C to +85°C                                    |  |  |
| Storage Temperature  | -65°C to +125°C                                   |  |  |

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.
- 5. When the RF input is applied to the terminated port, the absolute maximum power is +30 dBm.
- Standard CMOS TTL interface, latch-up will occur if logic signal is applied prior to power supply.

### **Recommended PCB Configuration**



# Handling Procedures

Please observe the following precautions to avoid damage:

# **Static Sensitivity**

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

# Truth Table (Switch)

| C1 | RF1 | RF2 |
|----|-----|-----|
| 0  | On  | Off |
| 1  | Off | On  |

0 = TTL Low; 1 = TTL High

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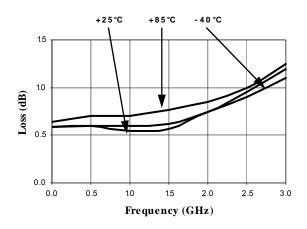


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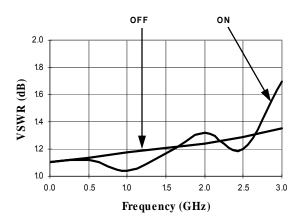
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# **Typical Performance Curves**

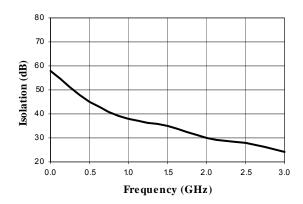
#### Typical Insertion Loss (dB)



#### Typical VSWR



#### Typical Isolation (dB)



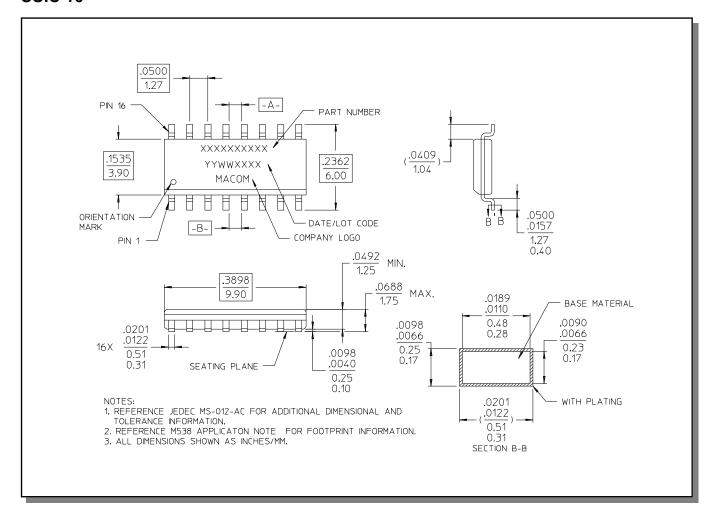
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# SOIC-16<sup>†</sup>



<sup>†</sup> Reference Application Note M538 for lead-free solder reflow recommendations.